75mΩ, 600V, Super Junction N-Channel Power MOSFET SRC60R075FBS

General Description

The Sanrise SRC60R075FBS is a high voltage power MOSFET, fabricated using advanced super junction technology. The resulting device has extremely low on resistance, low gate charge and fast switching time, making it especially suitable for applications which require superior power density and outstanding efficiency.

The SRC60R075FBS break down voltage is 600V and it has a high rugged avalanche characteristics.

The SRC60R075FBS is available in TO-263-2，TO-220F, TO-220C and TO-247 packages.

Symbol

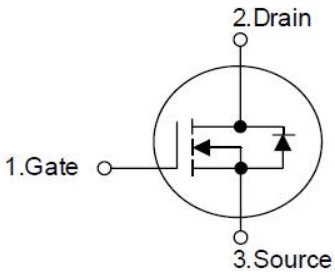


Figure 1 Symbol of SRC60R075FBS

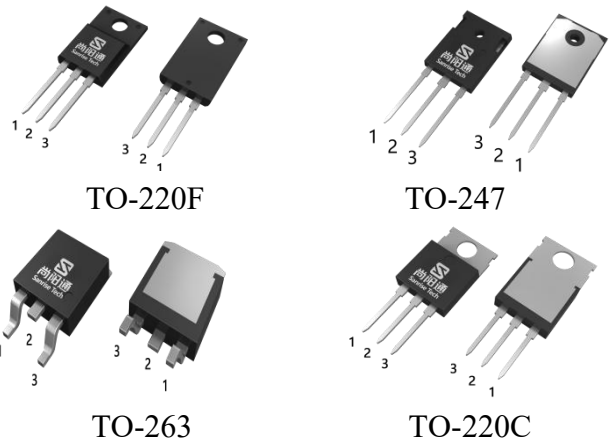
Features

- Ultra Low $R_{DS(ON)}$ = 75mΩ @ V_{GS} = 10V.
- Ultra Low Gate Charge, Qg=69nC typ.
- Fast switching capability
- Robust design with better EAS performance
- Optimized switching process
- Non-automotive Qualified
- Ultra-fast body diode

Application

- EV Charger
- High Performance PS

Package Type



TO-220F TO-247

TO-263 TO-220C

Figure 2 Package Types of SRC60R075FBS

Ordering Information

SRC60R075FBS□□–□

Circuit Type

Package
T: TO-247
S2: TO-263-2
TF: TO-220F
TC: TO-220C

E: Lead Free
G: Green
Blank: Tube
TR: Tape & Reel

Package	Part Number	Marking ID	Packing Type
TO-247	SRC60R075FBST-G	SRC60R075FBSTG	Tube
TO-220F	SRC60R075FBSTF-G	SRC60R075FBSTFG	Tube
TO-263-2	SRC60R075FBSS2TR-G	SRC60R075FBSS2G	Tape & Reel
TO-220C	SRC60R075FBSTC-G	SRC60R075FBSTCG	Tube

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Absolute Maximum Ratings[Note 1]

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage (static)		V_{GSS}	±20	V
Gate-Source Voltage (dynamic), AC (f>1 Hz)		V_{GSS}	±30	V
Continuous Drain Current	T_C=25ºC	I_D	34	A
	T_C=100ºC		21	
	T_C=125ºC		15	
Power Dissipation（Tc=25℃,TO-220F）		P_{tot}	31.2	W
Power Dissipation（Tc=25℃,TO-247,TO-220C,TO-263）		P_{tot}	219.2	W
Pulsed Drain Current (Note 2)		I_{DM}	102	A
Avalanche Energy, Single Pulse (Note 3)		E_{AS}	320	mJ
Avalanche Energy, Repetitive (Note 2)		E_{AR}	0.1	mJ
Avalanche Current, Repetitive (Note 2)		I_{AR}	4.0	A
Continuous Diode Forward Current		I_S	34	A
Diode Pulse Current		$I_{S.PULSE}$	102	A
MOSFET dv/dt Ruggedness, V_{DS}<=480V		dv/dt	80	V/ns
Reverse Diode dv/dt, V_{DS}<=480V, I_{SD}<=I_D		dv/dt	50	V/ns
Operating Junction Temperature		T_J	150	ºC
Storage Temperature		T_{STG}	-55 to 150	ºC
Lead Temperature (Soldering, 10 sec)		T_{LEAD}	260	ºC

Note:
1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. I_{AS} =4.0A, V_{DD} = 60V, R_G = 25Ω, Starting T_J = 25°C

Thermal Resistance

Parameter		Symbol	Min	Typ	Max	Unit
Thermal resistance, Junction-to-Case	TO-220F	R_{thJC}			4	ºC /W
	TO-220C				0.57	
	TO-247				0.57	
	TO-263				0.57	
Thermal resistance, Junction-to-Ambient	TO-220F	R_{thJA}			72	ºC /W
	TO-220C				60	
	TO-247				60	
	TO-263				60	

Electrical Characteristics

T_J = 25℃, unless otherwise specified.

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250uA	600			V
Zero Gate Voltage Drain Current		I_{DSS}	V_{DS}=600V, V_{GS}=0V			20	uA
Gate-Body Leakage Current	Forward	I_{GSSF}	V_{GS}=20V, V_{DS}=0V			100	nA
	Reverse	I_{GSSR}	V_{GS}=-20V, V_{DS}=0V			-100	
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=0.25mA	4.0	5.0	6.0	V
Static Drain-Source On-Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=24A		60	75	mΩ
Gate Resistance		R_G	f=1MHz, Open Drain		1.0		Ω
Dynamic Characteristics							
Input Capacitance		C_{ISS}	V_{DS}=400V, V_{GS}=0V, f=100kHz		2772		pF
Output Capacitance		C_{OSS}			78		pF
Effective output capacitance, energy related NOTE5		$C_{O(er)}$	V_{GS}=0V, V_{DS}=0…480V		65		pF
Effective output capacitance, time related NOTE6		$C_{O(tr)}$			729		
Turn-on Delay Time		$t_{d(on)}$	V_{DD}=400V, I_D=24A R_G=3Ω, V_{GS}=12V		72		ns
Rise Time		t_r			19		
Turn-off Delay Time		$t_{d(off)}$			40		
Fall Time		t_f			8		
Gate Charge Characteristics							
Gate to Source Charge		Q_{gs}	V_{DD}=400V, I_D=24A V_{GS}=0 to 10V		21		nC
Gate to Drain Charge		Q_{gd}			32		
Gate Charge Total		Q_g			69		
Gate Plateau Voltage		$V_{plateau}$			7.2		V
Reverse Diode Characteristics							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS}=0V, I_{SD}=24A		0.9	1.1	V
Reverse Recovery Time		t_{rr}	V_R=400V, I_F=24A dI$_F$/dt=120A/us		197		ns
Reverse Recovery Charge		Q_{rr}			2.0		uC
Peak Reverse Recovery Current		I_{rrm}			18.5		A

Note:

5. $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 480V

6. $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 480 V

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Shenzhen Sanrise Technology Co., LTD.

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Main Site:

- Headquarter

Shenzhen Sanrise Technology Co., LTD.

A1206, Skyworth building, No. 008, gaoxinnan 1st Road, Gaoxin District, Yuehai street,, Nanshan District, ShenZhen, P.R.China

Tel: +86-755-22953335

Fax: +86-755-22916878

- Shanghai Office

Shenzhen Sanrise Technology Co., LTD.

Rm.401, Building B, No. 666, Zhangheng Road, Zhangjiang Hi-Tech Park, Shanghai, P.R.China

Tel: +86-21-68825918